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Vishay Siliconix

# Automotive N-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	40				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0017				
I <sub>D</sub> (A)	120				
Configuration	Single				

# TO-263

### Top View N-Channel MOSFET

### **FEATURES**

- TrenchFET® Power MOSFET
- · Package with Low Thermal Resistance
- AEC-Q101 Qualifiedd
- 100 % R<sub>a</sub> and UIS Tested
- Material categorization:
  For definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>





ROHS COMPLIANT HALOGEN FREE

ORDERING INFORMATION	
Package	TO-263
Lead (Pb)-free and Halogen-free	SQM120N04-1m7-GE3

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage		$V_{DS}$	40	V		
Gate-Source Voltage		$V_{GS}$	± 20	V		
Continuous Drain Currenta	T <sub>C</sub> = 25 °C	1	120			
Continuous Drain Current	T <sub>C</sub> = 125 °C	I <sub>D</sub>	120			
Continuous Source Current (Diode Conduction)	I <sub>S</sub>	120	Α			
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	480				
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	85			
Single Pulse Avalanche Energy	L = 0.1 IIII1	E <sub>AS</sub>	361	mJ		
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	$P_{D}$	375	W		
Maximum Fower Dissipation	T <sub>C</sub> = 125 °C		125	VV		
Operating Junction and Storage Temperature R	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C			

THERMAL RESISTANCE RATINGS							
PARAMETER		SYMBOL	LIMIT	UNIT			
Junction-to-Ambient F	PCB Mount <sup>c</sup>	$R_{thJA}$	40	°C/W			
Junction-to-Case (Drain)		$R_{thJC}$	0.4	C/VV			

### **Notes**

- a. Package limited.
- b. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static	•					·		
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0$ , $I_D = 250 \mu A$		40	-	-	V	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	· V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.5	3.0	3.5	V	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	=.	-	± 100	nA	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V	=.	-	1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 175 °C	-	-	250		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	120	-	=-	Α	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 30 A	-	0.0014	0.0017	Ω	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 30 A, T <sub>J</sub> = 125 °C	-	-	0.0027		
	, ,	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 30 A, T <sub>J</sub> = 175 °C	-	-	0.0033		
Forward Transconductance <sup>b</sup>	9fs	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 30 A		-	198	-	S	
Dynamic <sup>b</sup>								
Input Capacitance	C <sub>iss</sub>			=.	13 880	17 350	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	=.	5720	7150		
Reverse Transfer Capacitance	C <sub>rss</sub>	1		-	840	1050		
Total Gate Charge <sup>c</sup>	Qg			-	206	310		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 20 \text{ V}, I_{D} = 120 \text{ A}$	=.	50	=-	nC	
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$	1		=.	44			
Gate Resistance	$R_g$		f = 1 MHz	0.57	1.14	1.71	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	26	39		
Rise Time <sup>c</sup>	t <sub>r</sub>	V <sub>DD</sub> =	$V_{DD} = 20 \text{ V}, R_1 = 0.17 \Omega$		21	32	- ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 120 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		-	68	102		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	12	18		
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>				•			
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	480	Α	
Forward Voltage	$V_{SD}$	I <sub>F</sub> = 80 A, V <sub>GS</sub> = 0			0.86	1.5	V	

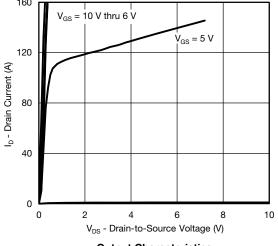
### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

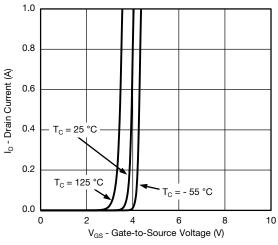
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



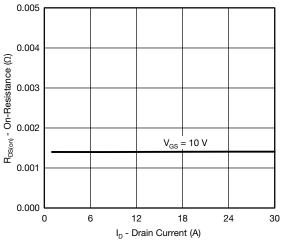
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



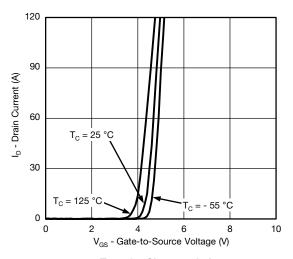
### **Output Characteristics**



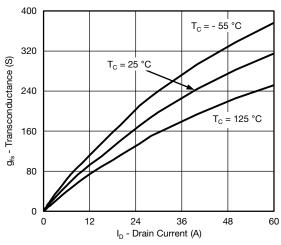
### **Transfer Characteristics**



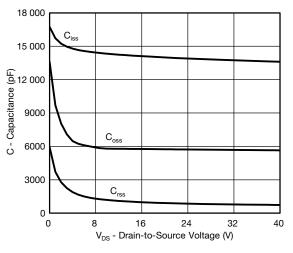
On-Resistance vs. Drain Current



### **Transfer Characteristics**



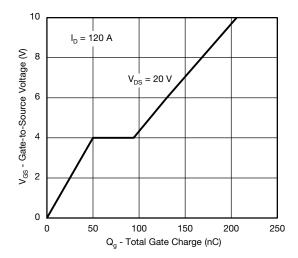
Transconductance



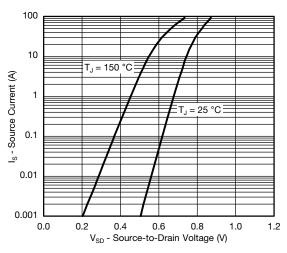
Capacitance



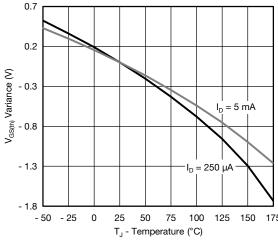
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



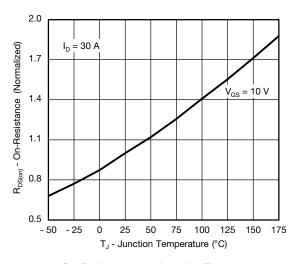
### **Gate Charge**



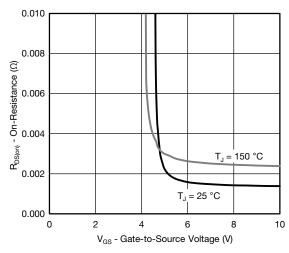
### Source Drain Diode Forward Voltage



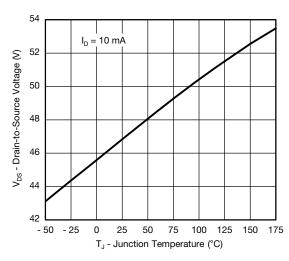
Threshold Voltage



### On-Resistance vs. Junction Temperature



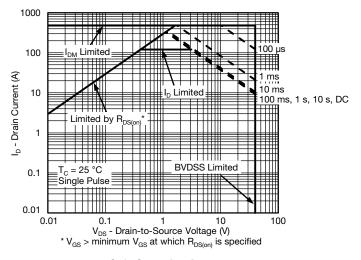
On-Resistance vs. Gate-to-Source Voltage



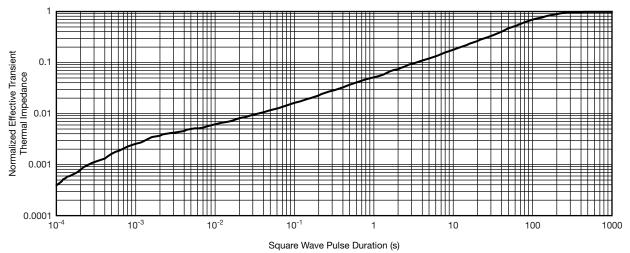
**Drain Source Breakdown vs. Junction Temperature** 



### **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



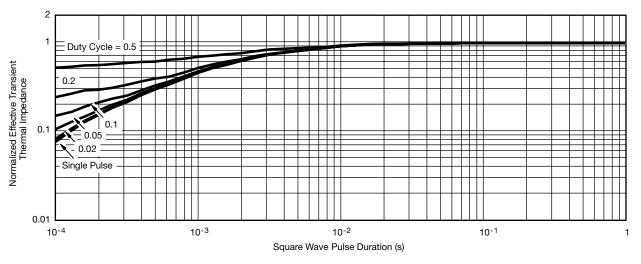
### Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



### Normalized Thermal Transient Impedance, Junction-to-Case

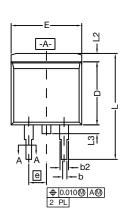
### Note

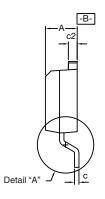
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction to Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

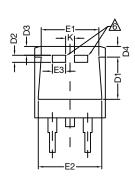
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# TO-263 (D<sup>2</sup>PAK): 3-LEAD

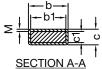








DETAIL A (ROTATED 90°)



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	SE	СТ	ION	ΙΔ.	- 1 - Δ	Ŧ

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. \*: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6 This feature is for thick lead.

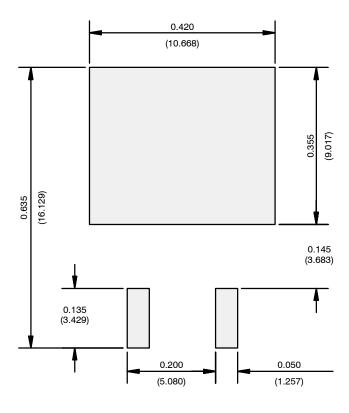
	INCHES		HES	MILLIMETERS		
	DIM.	MIN.	MAX.	MIN.	MAX.	
Α		0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457	
	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
	D3	0.045	0.055	1.143	1.397	
	D4	0.044	0.052	1.118	1.321	
	Е	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	-	
	E2	0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
	е	0.100	BSC	2.54 BSC		
	K	0.045	0.055	1.143	1.397	
	L	0.575	0.625	14.605	15.875	
L1		0.090	0.110	2.286	2.794	
L2		0.040	0.055	1.016	1.397	
	L3	0.050	0.070	1.270	1.778	
	L4	L4 0.010 BSC		0.254 BSC		
	М	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13						

DWG: 5843





### RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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